

- Typical  $R_{DS(ON)} = 32 \text{ m}\Omega$  @  $V_{GS} = 18 \text{ V}$
- Ultra Low Gate Charge  $(Q_{G(tot)} = 55 \text{ nC})$
- High Speed Switching with Low Capacitance (C<sub>oss</sub> = 114 pF)
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb–Free 2LI (on second level interconnection)
- SMPS, Solar Inverters, UPS, Energy Storage, EV Charging Infrastructure

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

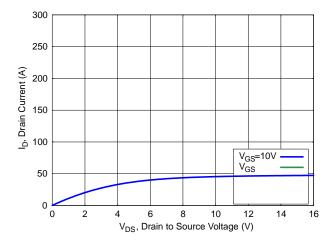
Drain-to-Source Voltage		$V_{DSS}$	650	V
Gate-to-Source Voltage		$V_{GS}$	-8/+22	V
Continuous Drain Current	$T_C = 25^{\circ}C$	$I_{D}$	50	Α

Thermal Resistance, Junction-to-Case (Note 4)	$R_{\theta JC}$	0.80	°C/W
Thermal Resistance, Junction-to-Ambient (Note 4)	$R_{\theta JA}$	40	

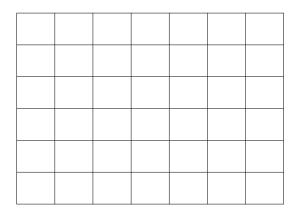
<sup>4.</sup> The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

Operation Values of Gate-to-Source Voltage

		L				
ırn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS} = -3/18 \text{ V}, V_{DD} = 400 \text{ V}, \\ I_{D} = 15 \text{ A}, R_{G} = 4.7 \Omega, T_{J} = 175^{\circ}\text{C} \\ 8 63.7228 698.57 \text{(NGR68-5,163)} 73.45 .9071 14.$	_	7.8	_	ns
urn-Off Delay Time	t <sub>d(OFT8 0 0</sub>	1D = 13 A, RG = 4.7 S2, TJ = 173 C 8 63.7228 698.57(N)386685,16373.95 .9071 14.	4 ref449.405	693.1288°	1 14.4 ref449	).405 693(d( <b>0</b> F
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DATE 16 SEP 2019

Α В Øp1 D2 Α E E1 **A2** Q E/2 D1 D Ø L1 b2 **A1** b1 (3X) Ĺ 1 4 С b(4X) e1 e 2X ⊕ 0.254 M B A M

